N-Channel Power MOSFET 24V, 9A, 15mΩ, Dual EMH8



http://onsemi.com

Features

- Low On-resistance
- 2.5V drive
- Common-Drain Type
- Protection diode in
- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

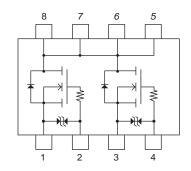
Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	24	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ΙD	9	Α
Drain Current (Pulse)	IDP	40	Α
PW≤10μs, duty cycle≤1%			
Power Dissipation	PD	1.3	W
When mounted on ceramic substrate(900mm ² ×0.8mm) 1unit			
Total Dissipation	PT	1.4	W
When mounted on ceramic substrate(900mm ² ×0.8mm)			
JunctionTemperature	Tj	150	°C
Storage Temperature	Tstg	- 55 to	°C
Otorage remperature		+150	

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient	R_{θ} JA	96	°C/W
When mounted on ceramic substrate(900mm ² ×0.8mm)			

Electrical Connection

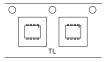
N-channel



Marking



Packing Type:TL



Ordering & Package Information

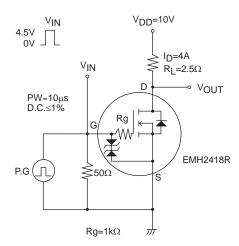
Device	Package	Shipping
EMH2418R-TL-H		2,000
Pb-free and	EMH8	3,000
Halogen Free		pcs. / reel

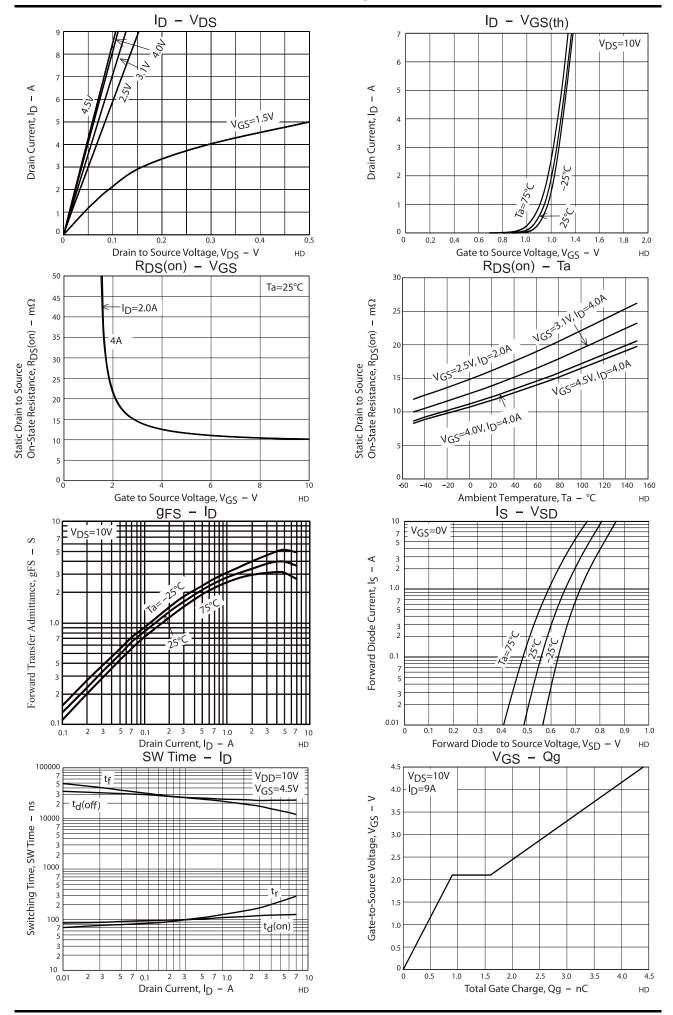
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

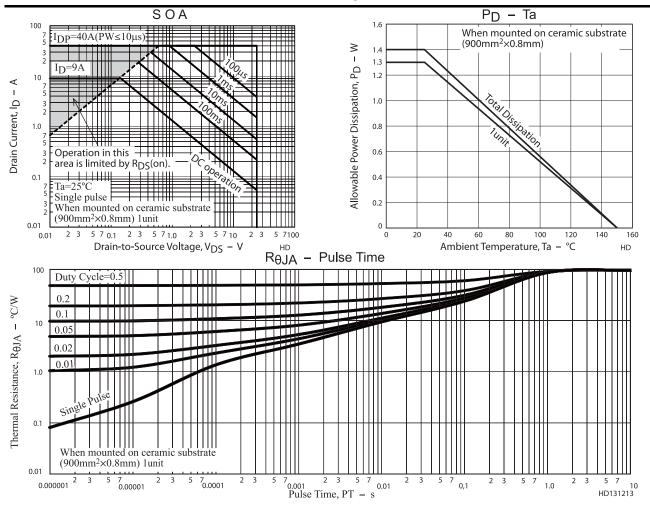
Electrical Characteristics at Ta = 25°C

Parameter	O. week ed	0 - 199	Value			11.26
	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	24			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±1	μА
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	0.5		1.3	V
Forward Transconductance	gFS .	V _{DS} =10V, I _D =4A		4		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =4A, V _{GS} =4.5V	9.6	12	15	mΩ
	R _{DS} (on)2	I _D =4A, V _{GS} =4.0V	10.0	12.5	16.3	mΩ
	R _{DS} (on)3	I _D =4A, V _{GS} =3.1V	11.3	14.2	20	mΩ
	R _{DS} (on)4	I _D =2A, V _{GS} =2.5V	13.2	16.5	23.1	mΩ
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		120		ns
Rise Time	t _r			170		ns
Turn-OFF Delay Time	t _d (off)			17500		ns
Fall Time	tf			22600		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4.5V, I _D =9A		4.4		nC
Gate to Source Charge	Qgs			0.9		nC
Gate to Drain "Miller" Charge	Qgd			0.7		nC
Forward Diode Voltage	V _{SD}	I _S =9A, V _{GS} =0V		0.8	1.2	V

Switching Time Test Circuit







Package Dimensions

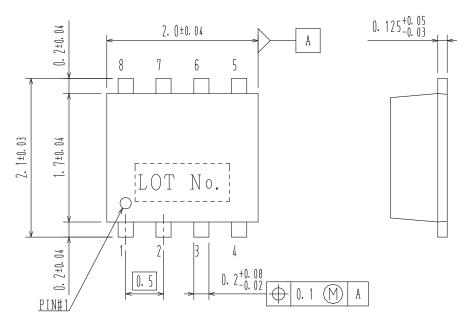
EMH2418R-TL-H

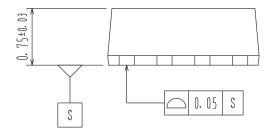
SOT-383FL/EMH8

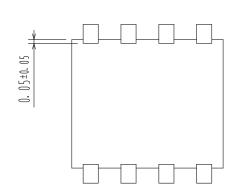
CASE419AT ISSUE O

Unit: mm

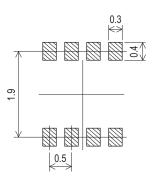
- 1: Source1
- 2: Gate1
- 3: Source2
- 4: Gate2
- 5: Drain
- 6: Drain
- 7: Drain
- 8: Drain







Soldering Footprint



Note on usage: Since the EMH2418R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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